

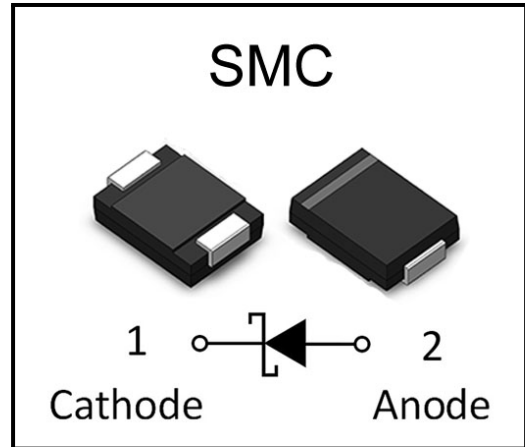
SS32-SS320

Schottky Barrier Diode

Features

- For surface mounted applications
- Metal silicon junction, majority carrier conduction
- Low power loss, high efficiency
- Built-in strain relief, ideal for automated placement
- High forward surge current capability
- High temperature soldering guaranteed:
250°C/10 seconds at terminals

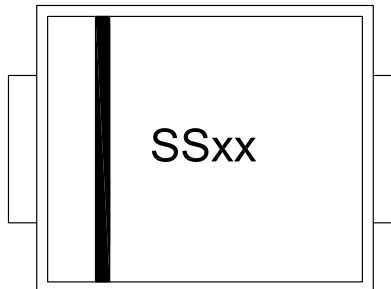
Package



Description

- Case: JEDEC DO-214AB molded plastic
- Terminals: Axial leads. Solderable per MIL-STD-750 Method 2026
- Polarity: Color band denotes cathode
- Mounting Position: Any

Marking



Ordering information

Part Number	SS32	SS33	SS34	SS35	SS36	SS38	SS310	SS315	SS320
Marking	SS32	SS33	SS34	SS35	SS36	SS38	SS310	SS315	SS320
Base qty	3K	3K	3K	3K	3K	3K	3K	3K	3K



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Maximum Ratings and Electrical Characteristics@T_A=25°C unless otherwise noted

Symbol	Parameters	SS 32	SS 33	SS 34	SS 35	SS 36	SS 38	SS 310	SS 315	SS 320	Units
V _{RRM}	Maximum Recurrent Peak Reverse Voltage	20	30	40	50	60	80	100	150	200	V
V _{RMS}	Maximum RMS Voltage	14	21	28	35	42	56	70	105	140	V
V _{DC}	Maximum DC Blocking Voltage	20	30	40	50	60	80	100	150	200	V
I _{AV}	Maximum Average Forward Rectified Current	3.0									A
I _{FSM}	Peak Forward Surge Current 8.3ms single half sine-wave superimposed on rated	70									A
V _F	Maximum Forward Voltage at 1.0A DC	0.55			0.70		0.85		0.95		V
I _R	Maximum DC reverse current@T _A =25°C	0.50						0.10			mA
	Maximum DC reverse current@T _A =100°C	10						5			
R _{θJA} ⁽¹⁾	Typical Thermal Resistance	55									°C/W
T _J	Operating Junction Temperature Range	-55 to +150						-55 to +175			°C
T _{STG}	Storage Temperature Range	-55 to +150									°C

Note:(1)Thermal resistance from junction to ambient and from junction to lead mounted on P.C.B. with 0.6" x 0.6" (16 mm x 16 mm) copper pad areas



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Typical Performance Characteristics($T_J = 25^\circ\text{C}$, unless otherwise noted)

Figure 1: $I_{AV}-T_A$ Curve

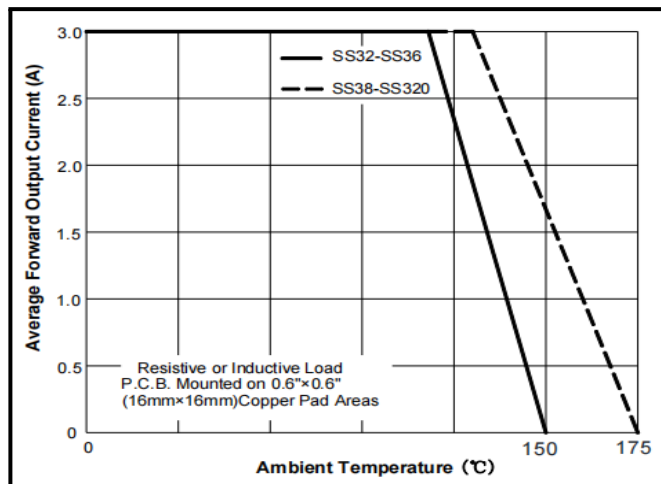


Figure 2: Surge Forward Current Capability

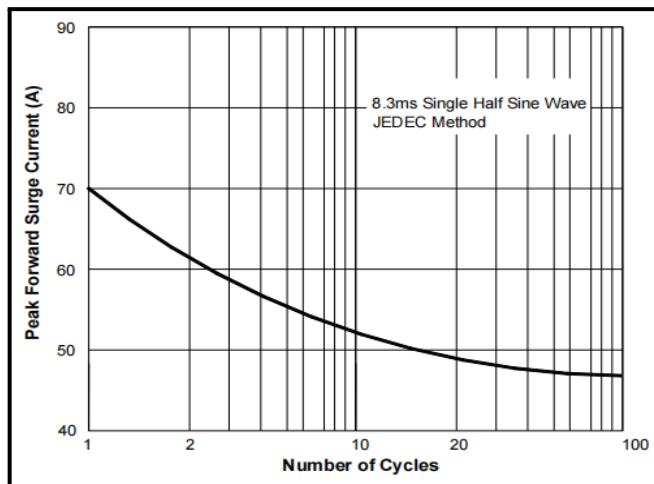


Figure 3: Forward Voltage

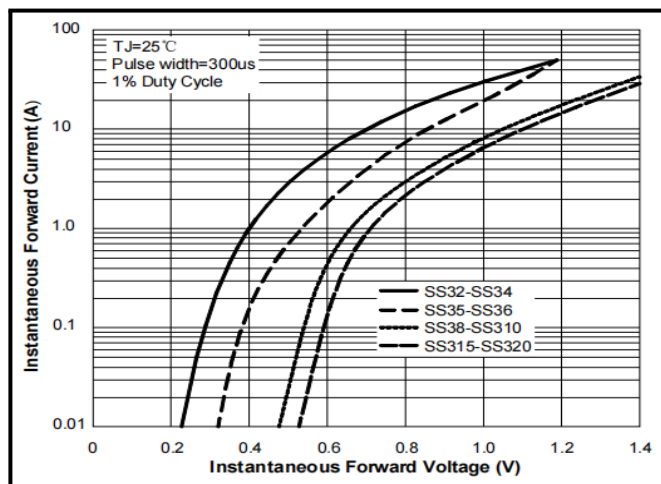
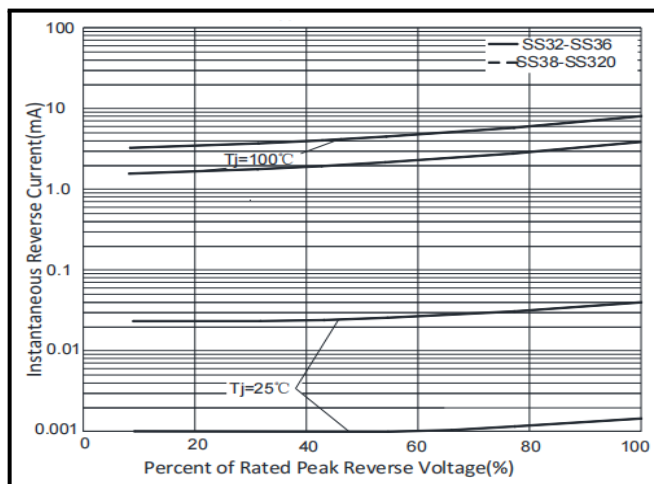


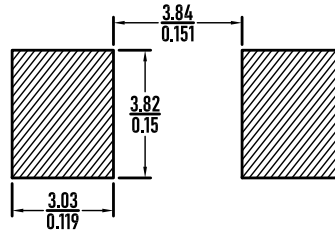
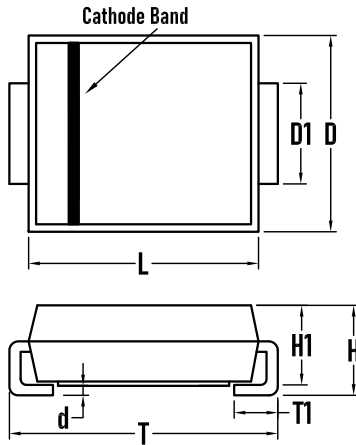
Figure 4: Typical Reverse Characteristics



SS32-SS320

Schottky Barrier Diode

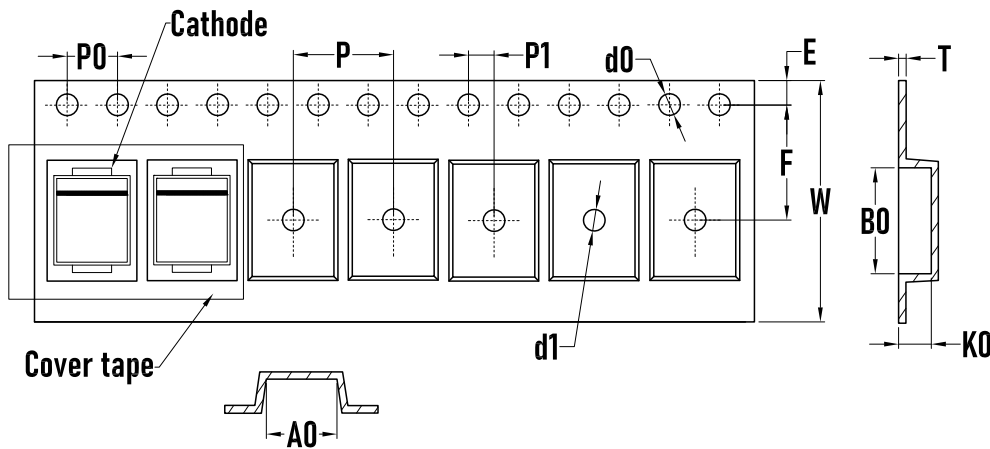
Package Mechanical Data - SMC



Note:
dimensions: $\frac{\text{mm}}{\text{inch}}$

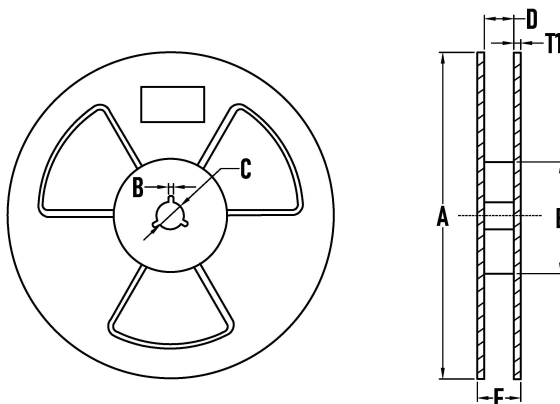
SYMBOL	MILLIMETER	
	MIN	MAX
D	5.75	6.15
D1	2.70	3.30
T	7.65	8.25
T1	0.90	1.50
d	—	0.3
H1	2.07	2.47
H	2.20	2.60
L	6.70	7.10

Packaging Tape - SMC



SYMBOL	MILLIMETER
A0	6.00±0.1
B0	8.25±0.02
d0	1.50±0.1
d1	1.50±0.1
E	1.75±0.1
F	7.50±0.1
K0	2.70±0.1
P	8.00±0.1
P0	4.00±0.1
P1	2.00±0.05
W	16.00±0.1
T	0.22±0.02

Packaging Reel



SYMBOL	MILLIMETER
A	323±2
B	3.0±0.2
C	15.0±0.5
D	16±2
E	73±2
T1	2.2±0.2
Quantity	3000PCS

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Specifications are subject to change without notice.

Please refer to <http://www.born-tw.com> for current information.

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